

UNISONIC TECHNOLOGIES CO., LTD

01N150V Preliminary Power MOSFET

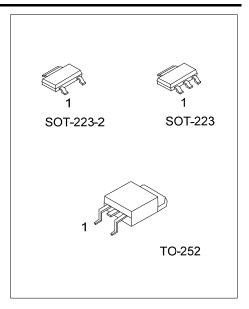
0.1A, 1500V N-CHANNEL POWER MOSFET

■ DESCRIPTION

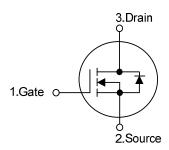
The UTC **01N150V** is a planar power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, low gate charge and superior switching performance.

■ FEATURES

- * $R_{DS(ON)} \le 130 \ \Omega \ @V_{GS} = 10V, I_D = 50mA$
- * High switching speed
- * 100% avalanche tested



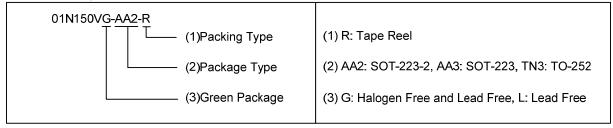
■ SYMBOL



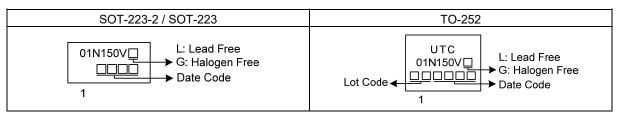
■ ORDERING INFORMATION

| Ordering Number | | Daakana | Pin Assignment | | | Da akin a | |
|-----------------|----------------|-----------|----------------|---|---|-----------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| 01N150VL-AA2-R | 01N150VG-AA2-R | SOT-223-2 | G | D | S | Tape Reel | |
| 01N150VL-AA3-R | 01N150VG-AA3-R | SOT-223 | G | D | S | Tape Reel | |
| 01N150VL-TN3-R | 01N150VG-TN3-R | TO-252 | G | D | S | Tape Reel | |

Note: Pin Assignment: G: Gate S: Source D: Drain



MARKING



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■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|----------------------|-------------------|------------------|------------|----------|
| Drain-Source Voltage | | V _{DSS} | 1500 | V |
| Gate-Source Voltage | | V _{GSS} | ±30 | V |
| Drain Current | Continuous | ID | 0.1 | Α |
| | Pulsed (Note 2) | I _{DM} | 0.2 | Α |
| Power Dissipation | SOT-223-2/SOT-223 | - | 0.9 | W |
| | TO-252 | P _D | 16 | W |
| Junction Temperature | | TJ | +150 | °C |
| Storage Temperature | | T _{STG} | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

■ THERMAL DATA

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---------------------|-------------------|--------|---------|------|
| Junction to Ambient | SOT-223-2/SOT-223 | 0 | 150 | °C/W |
| | TO-252 | θја | 110 | °C/W |
| Junction to Case | SOT-223-2/SOT-223 | 0 | 140 | °C/W |
| | TO-252 | θις | 7.8 | °C/W |

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate, t ≤ 10 sec.

■ ELECTRICAL CHARACTERISTICS

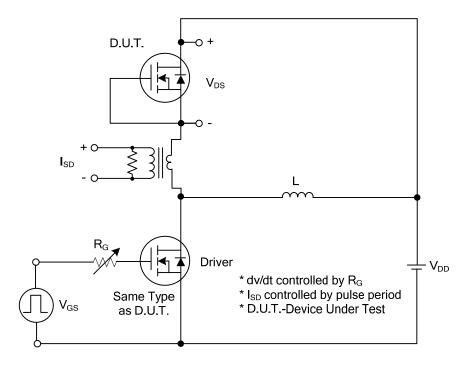
| PARAMETER | | SYMBOL | TEST CONDITIONS | | TYP | MAX | UNIT |
|---|-----------|---------------------|--|------|------|------|------|
| OFF CHARACTERISTICS | | | | | | _ | _ |
| Drain-Source Breakdown Voltage | | BV _{DSS} | I _D =250μA, V _{DS} =0V | 1500 | | | V |
| Drain-Source Leakage Current | | I _{DSS} | V _{DS} =1500V | | | 10 | μΑ |
| Gate-Source Leakage Current | Forward | Igss | V_{GS} =+30V, V_{DS} =0V | | | ±100 | nA |
| | Reverse | | V _{GS} =-30V, V _{DS} =0V | | | ±100 | nA |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | V _{DS} =V _{GS} , I _D =250µA | 1.0 | | 3.0 | V |
| Static Drain-Source On-State Resistance | | R _{DS(ON)} | V _{GS} =10V, I _D =50mA | | | 130 | Ω |
| DYNAMIC PARAMETERS | | | | | | | |
| Input Capacitance | | C _{ISS} | | | 100 | | pF |
| Output Capacitance | | Coss | V _{GS} =0V, V _{DS} =25V, f=1MHz | | 15 | | pF |
| Reverse Transfer Capacitance | | C _{RSS} | | | 2.5 | | pF |
| SWITCHING PARAMETERS | | | | | | | |
| Total Gate Charge | | Q _G | V _{DS} =1200V, V _{GS} =10V, I _D =0.1A | | 11.8 | | nC |
| Gate to Source Charge | | Q _G s | (Note1, 2) | | 2.1 | | nC |
| Gate to Drain Charge | | Q_{GD} | (140101, 2) | | 1.5 | | nC |
| Turn-ON Delay Time | | t _{D(ON)} | | | 4 | | ns |
| Rise Time | | t _R | V _{DS} =100V, V _{GS} =10V, I _D =0.1A, | | 19 | | ns |
| Turn-OFF Delay Time | | t _{D(OFF)} | R _G =25Ω (Note1, 2) | | 40 | | ns |
| Fall-Time | | t⊧ | | | 235 | | ns |
| SOURCE- DRAIN DIODE RATII | NGS AND C | CHARACTERI | STICS | | | | |
| Maximum Body-Diode Continuous Current | | Is | | | | 0.1 | Α |
| Maximum Body-Diode Pulsed Current | | Ism | | | | 0.2 | Α |
| Drain-Source Diode Forward Voltage | | V _{SD} | Is=0.1A | | | 1.4 | V |

Notes: 1. Pulse Test: Pulse width ≤150µs, Duty cycle ≤ 2%.

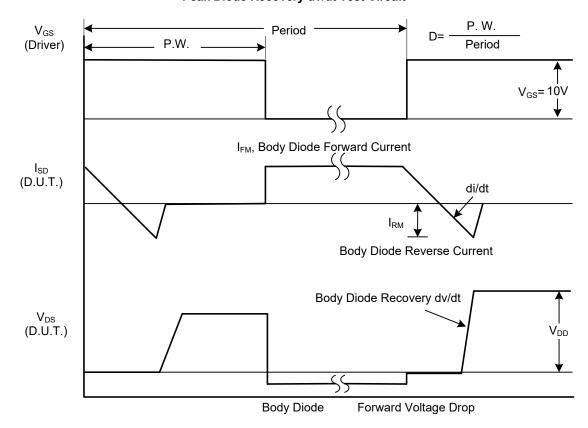
2. Essentially independent of operating temperature.



■ TEST CIRCUITS AND WAVEFORMS

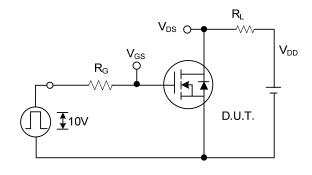


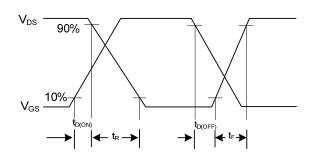
Peak Diode Recovery dv/dt Test Circuit



Peak Diode Recovery dv/dt Waveforms

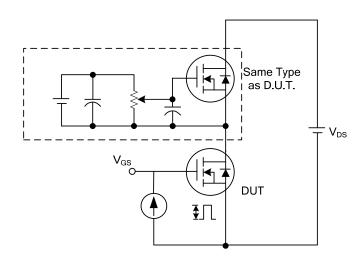
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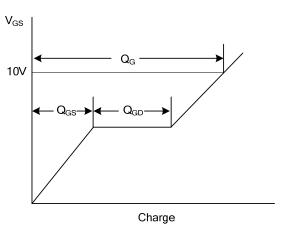




Switching Test Circuit

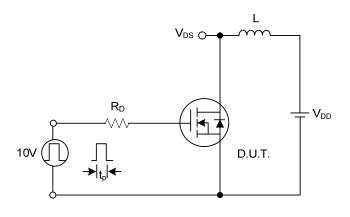
Switching Waveforms

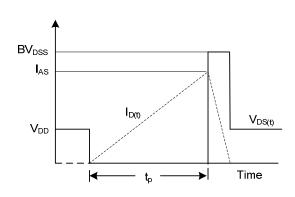




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

Unclamped Inductive Switching Waveforms

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